

IN THE CLAIMS

Please amend Claim 1 and add new Claims 9 to 13, as shown below. The claims, as pending in the subject application, read as follows:

1. (Currently Amended) A silicon-based film comprising a crystal phase formed on a substrate, ~~said~~ the substrate having a surface shape represented by a function f ,

wherein the surface shape has a standard deviation of an inclination $\arctan(df/dx)$ from 15° to 55° within the range of a sampling length dx from 20 nm to 100 nm,

wherein a Raman scattering strength resulting from an amorphous component in the silicon-based film is not more than a Raman scattering strength resulting from a crystalline component in the silicon-based film, and

wherein a difference between a spacing in a direction parallel to a principal surface of the substrate and a spacing of single crystal silicon is within the range of 0.2% to 1.0% with regard to the spacing of the single crystal silicon.

2. (Original) The silicon-based film according to claim 1, comprising a crystal of a columnar structure in a thickness direction.

3. (Original) The silicon-based film according to claim 1, wherein a percentage of a diffraction strength of (220) plane due to X-ray or electron beam diffraction is 30% or more of a total diffraction strength.

4. (Original) The silicon-based film according to claim 1, which is formed by a plasma CVD method using a high frequency.

5. (Original) The silicon-based film according to claim 4, wherein the high frequency is not less than 10 MHz but no more than 10 GHz.

6. (Original) A photovoltaic element comprising a silicon-based semiconductor layer having at least one pin junction on a support, wherein at least one i-type semiconductor layer comprises the silicon-based film as set forth in any one of claims 1 to 5.

7. (Original) The photovoltaic element according to claim 6, wherein the silicon-based semiconductor layer is formed on a substrate comprising at least a first transparent conductive layer stacked on the support, and the first transparent conductive layer has the surface shape represented by the function f .

8. (Original) The photovoltaic element according to claim 6, wherein the support is a conductive support.

9. (New) The silicon-based film according to claim 1, wherein the difference in spacings is achieved by promoting displacement of silicon atoms adhering to the substrate.

10. (New) The silicon-based film according to claim 9, wherein the displacement

of silicon atoms adhering to the substrate is promoted by activating ion bombardment at an early stage of formation of the silicon-based film.

11. (New) The silicon-based film according to claim 10, wherein the ion bombardment is activated by increasing high frequency power.

12. (New) The silicon-based film according to claim 10, wherein the ion bombardment is activated by introducing an inert gas.

13. (New) The silicon-based film according to claim 12, wherein the inert gas is argon.